

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
150V	22mΩ@10V	40A
	36mΩ@4.5V	



合肥矽普半导体

Siliup Semiconductor Technology Co., Ltd

技术 品质 服务

www.siliup.com

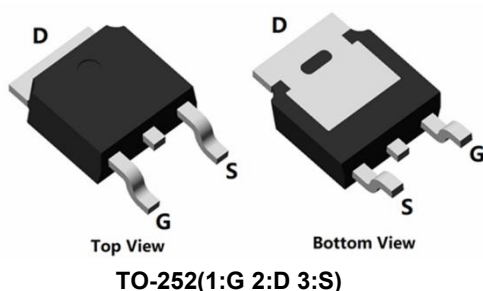
Feature

- Fast Switching
- Low Gate Charge and $R_{ds(on)}$
- Advanced Split Gate Trench Technology
- **100% UIS TESTED**

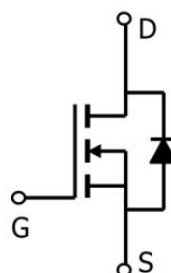
Applications

- Power switching application
- DC-DC Converter
- Power Management

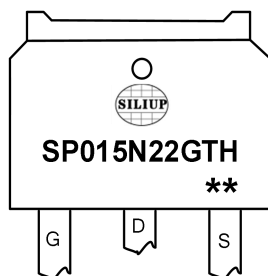
Package



Circuit diagram



Marking



SP015N22GTH : Product code
** : Week code

Order Information

Device	Package	Unit/Tube
SP015N22GTH	TO-252	2500

Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	150	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current (Tc=25°C)	I _D	40	A
Continuous Drain Current (Tc=100°C)	I _D	27	A
Pulsed Drain Current	I _{DM}	160	A
Single Pulse Avalanche Energy ¹	E _{AS}	196	mJ
Power Dissipation (Tc=25°C)	P _D	85	W
Power Dissipation (Tc=100°C)	P _D	34	W
Thermal Resistance Junction-to-Case	R _{θJC}	1.47	°C/W
Storage Temperature Range	T _{STG}	-55 to 150	°C
Operating Junction Temperature Range	T _J	-55 to 150	°C

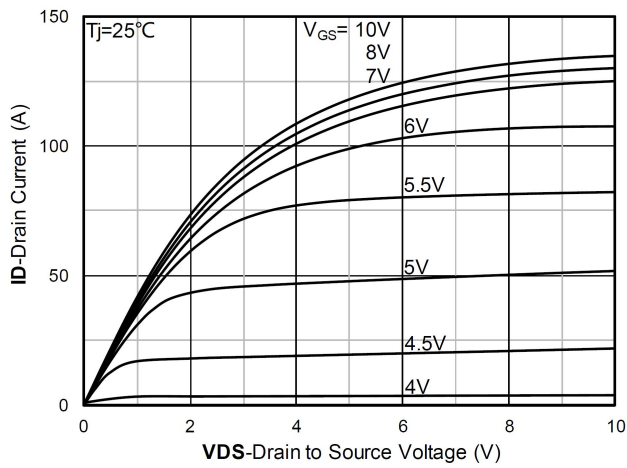
Electrical characteristics (Ta=25°C, unless otherwise noted)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	ID=250μA , VGS=0V	150	-	-	V
Drain Cut-Off Current	I _{DSS}	VDS=120V , VGS=0V	-	-	1	μA
Gate Leakage Current	I _{GSS}	VGS=±20V , VDS=0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	VDS=VGS , ID=250μA	1.6	2.0	2.6	V
Drain-Source ON Resistance	R _{DS(ON)}	VGS=10V , ID=20A	-	22	28	mΩ
		VGS=4.5V , ID=10A	-	36	-	
Gate Resistance	R _G	f=1MHz	-	0.06	-	Ω
Dynamic Characteristics						
Input Capacitance	C _{iss}	VDS=75V , VGS=0V , f=1.0MHz	-	887	-	pF
Output Capacitance	C _{oss}		-	137	-	
Reverse Transfer Capacitance	C _{rss}		-	15	-	
Total Gate Charge	Q _g	VDS=75V , VGS=10V , ID=10A	-	13	-	nC
Gate-Source Charge	Q _{gs}		-	4.4	-	
Gate-Drain Charge	Q _{gd}		-	2.4	-	
Gate Plateau Voltage	V _{plateau}		-	4	-	V
Switching Characteristics						
Turn-On Delay Time	t _{d(on)}	VDS=75V , VGS=10V , ID=10A , RG=6Ω	-	14	-	nS
Rise Time	t _r		-	5.6	-	
Turn-Off Delay Time	t _{d(off)}		-	17	-	
Fall Time	t _f		-	3.2	-	
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V _{SD}	IS=1A , VGS=0V , TJ=25℃	-	-	1.2	V
Maximum Body-Diode Continuous Current	I _S		-	-	40	A
Body Diode Reverse Recovery Time	T _{rr}	IS=10A , di/dt=100A/us , TJ=25℃	-	42	-	nS
Body Diode Reverse Recovery Charge	Q _{rr}		-	125	-	nC

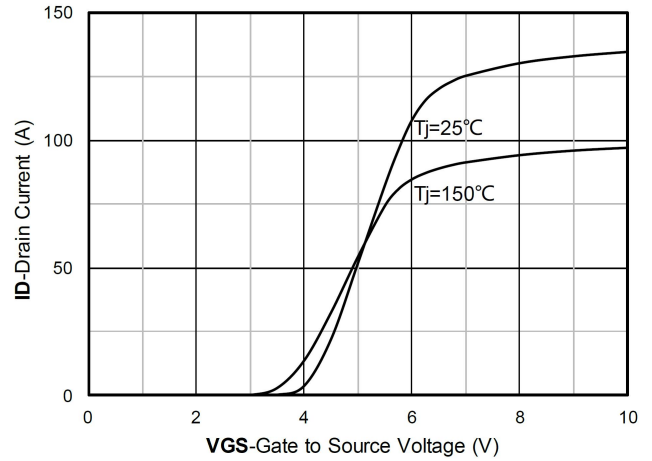
Note :

1. The test condition is VDD=50V, VGS=10V, L=0.5mH, RG=25Ω;

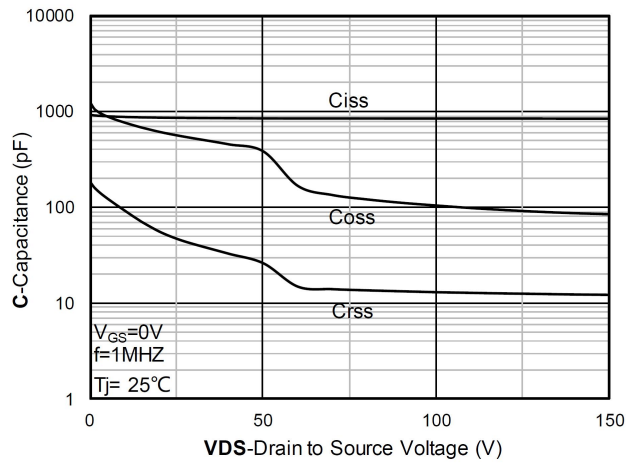
Typical Characteristic



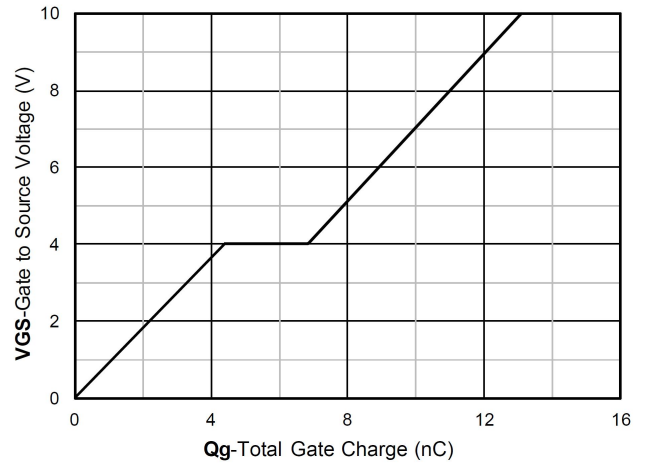
Output Characteristics



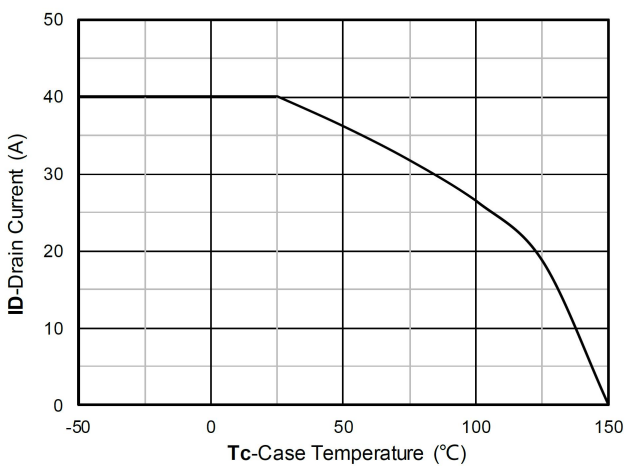
Transfer Characteristics



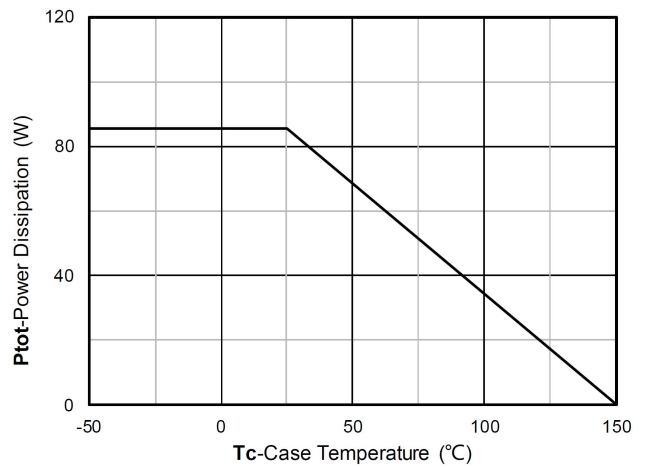
Capacitance Characteristics



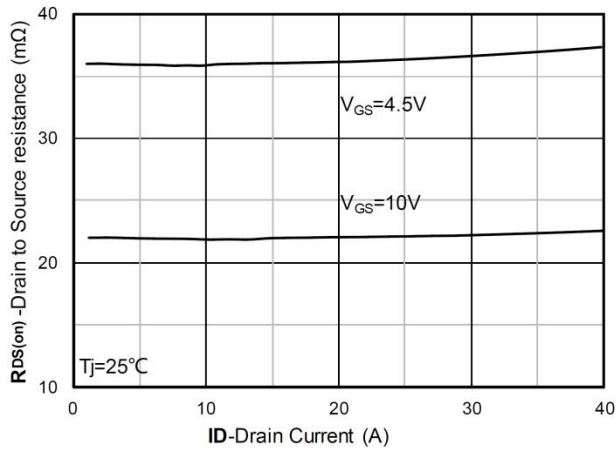
Gate Charge



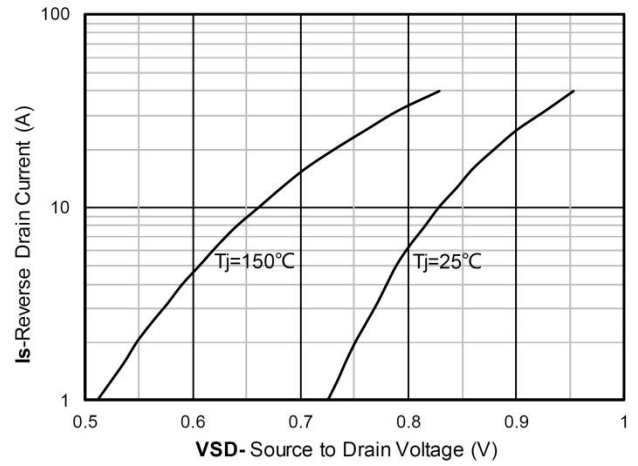
Current dissipation



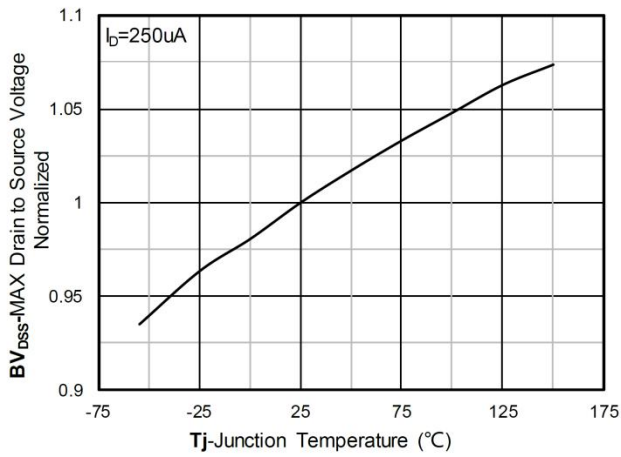
Power dissipation



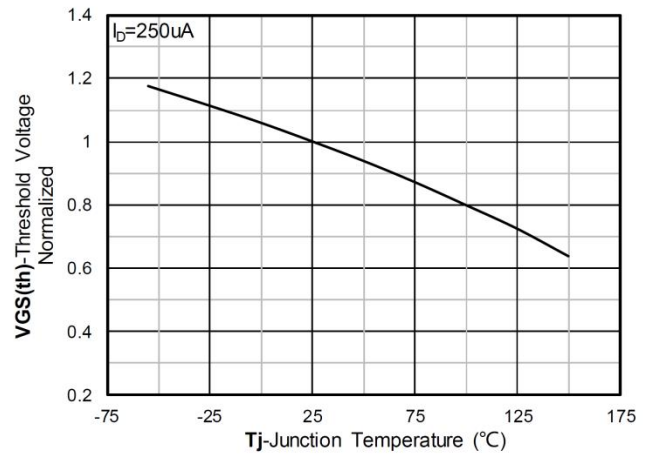
RDS(on) VS Drain Current



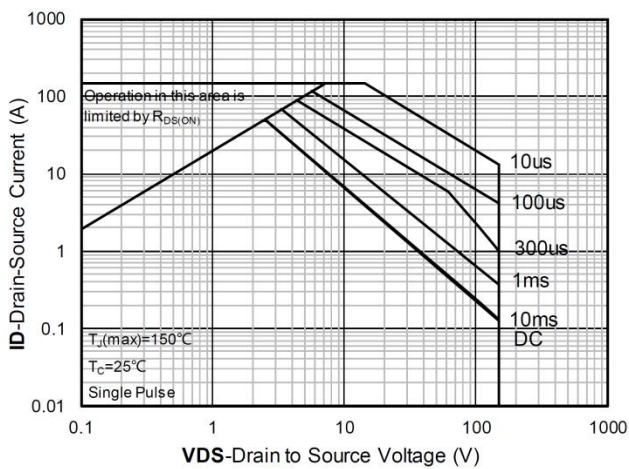
Forward characteristics of reverse diode



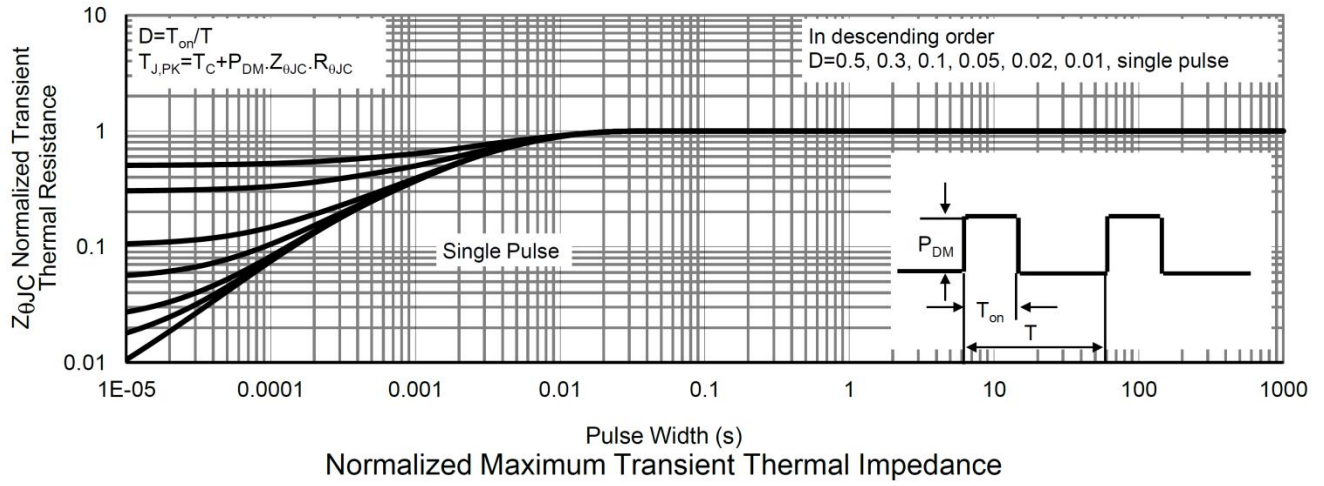
Normalized breakdown voltage



Normalized Threshold voltage

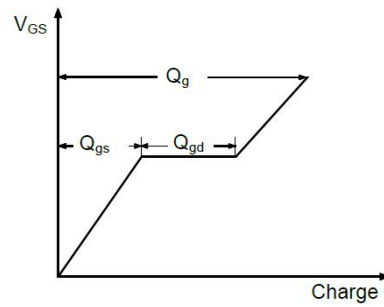
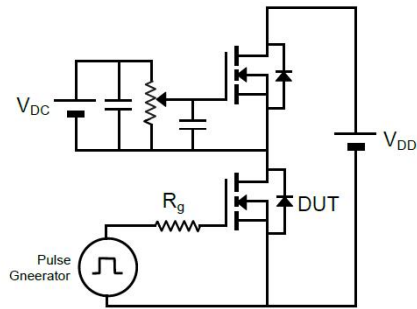


Safe Operation Area

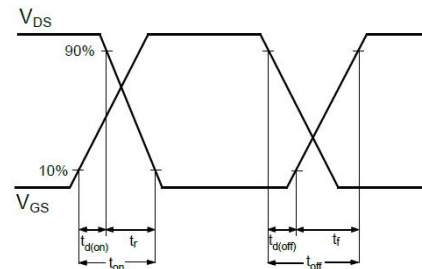
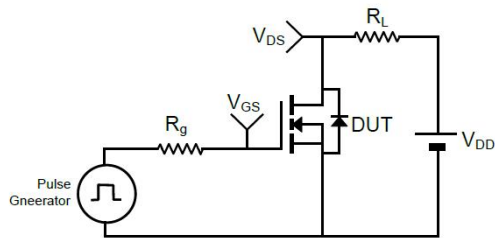


Test Circuit

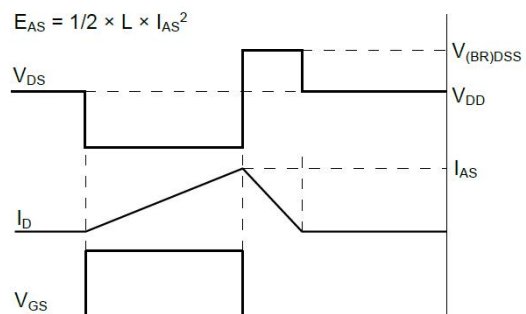
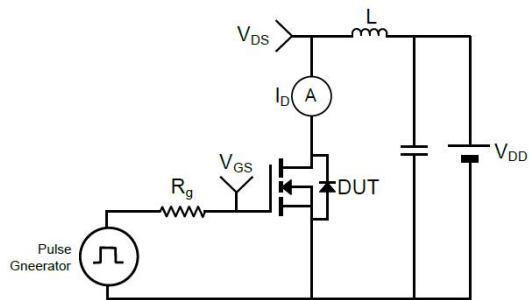
Gate Charge



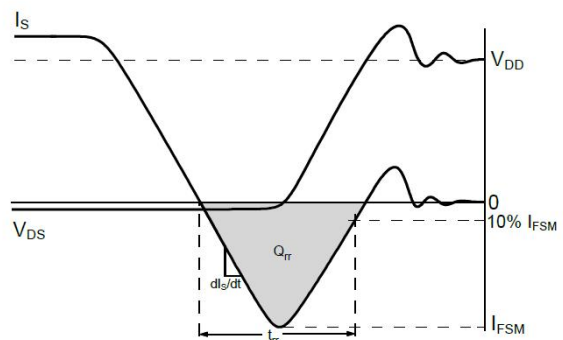
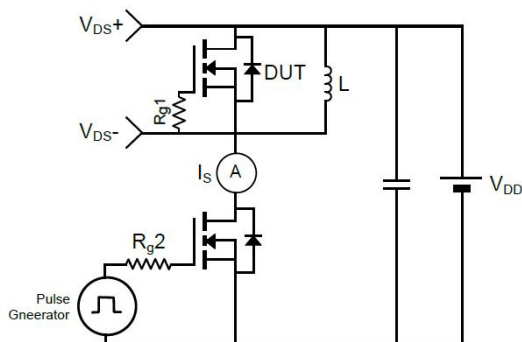
Resistive Load Switching Time

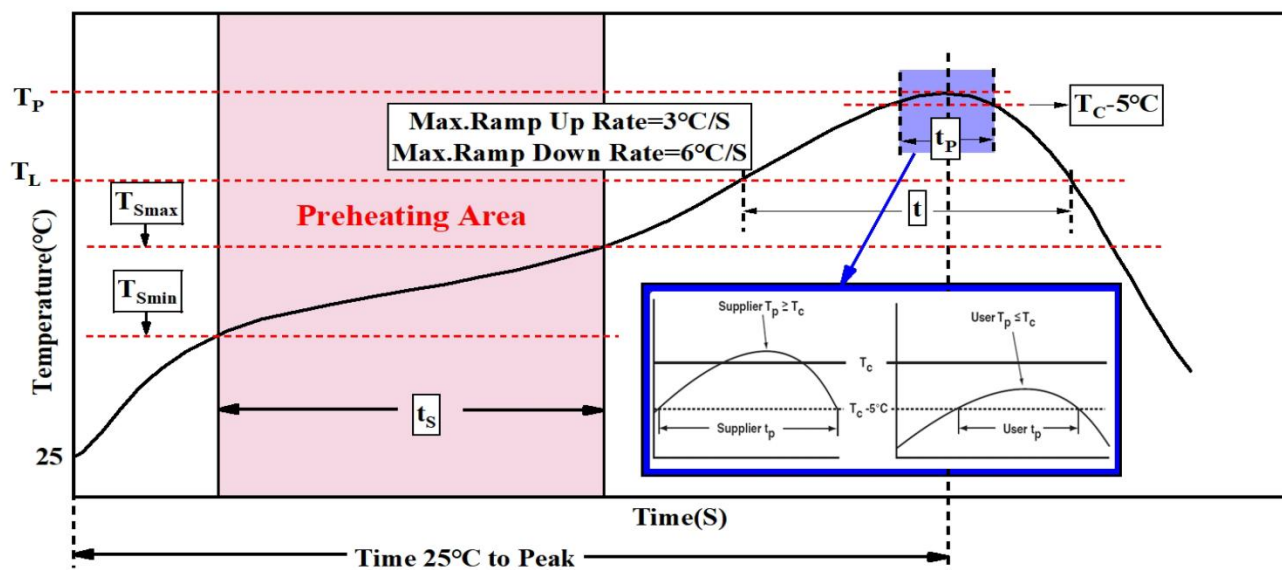


Un-clamped Inductive Load Switching



Drain-Source Body Diode Reverse Recovery



Temperature Profile for IR Reflow Soldering


Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T _{smin})	100°C	150°C
Temperature max (T _{smax})	150°C	200°C
Time (T _{smin} to T _{smax}) (t _s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T _{smax} to T _p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T _L)	183 °C	217°C
Time at liquidous (t _L)	60-150 seconds	60-150 seconds
Peak package body Temperature e (T _p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t _p)** within 5°C of the specified classification temperature (T _c)	20** seconds	30** seconds
Average ramp-down rate (T _p to T _{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T _p) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t _p) is defined as a supplier minimum and a user maximum		

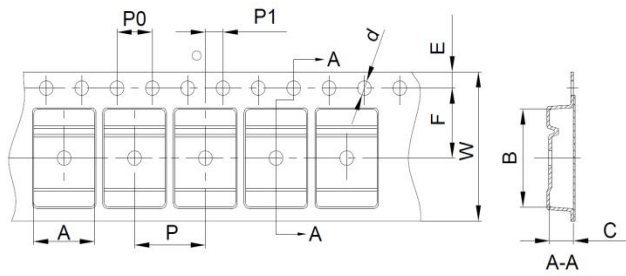
Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

TO-252 Embossed Carrier Tape



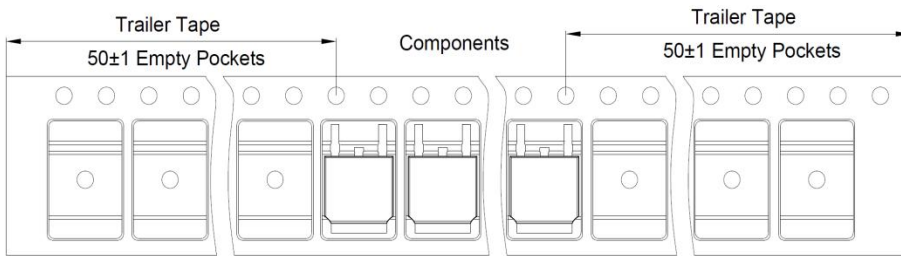
Packaging Description:

TO-252 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Hear Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2500 units per 13" or 33.0 cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

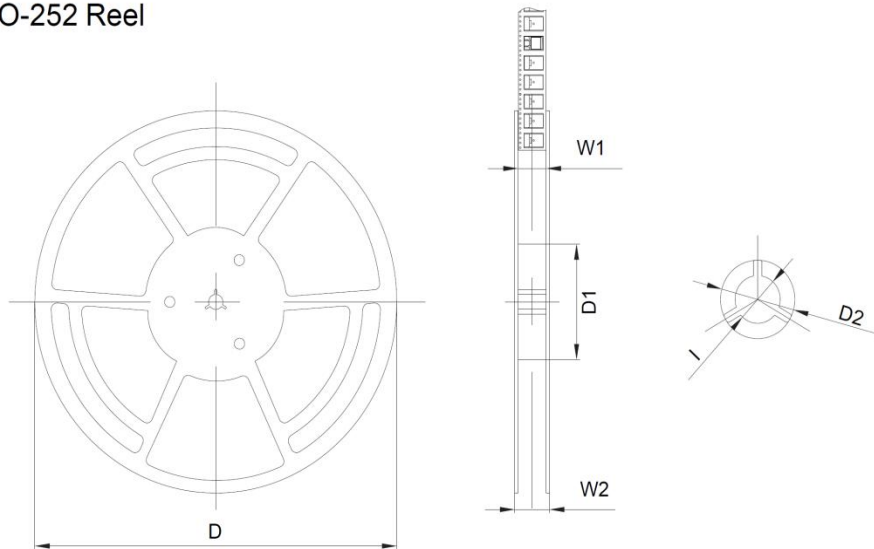
Dimensions are in millimeter

Pkg type	A	B	C	d	E	F	P0	P	P1	W
TO-252	6.90	10.50	2.70	Φ1.55	1.75	7.50	4.00	8.00	2.00	16.00

TO-252 Tape Leader and Trailer



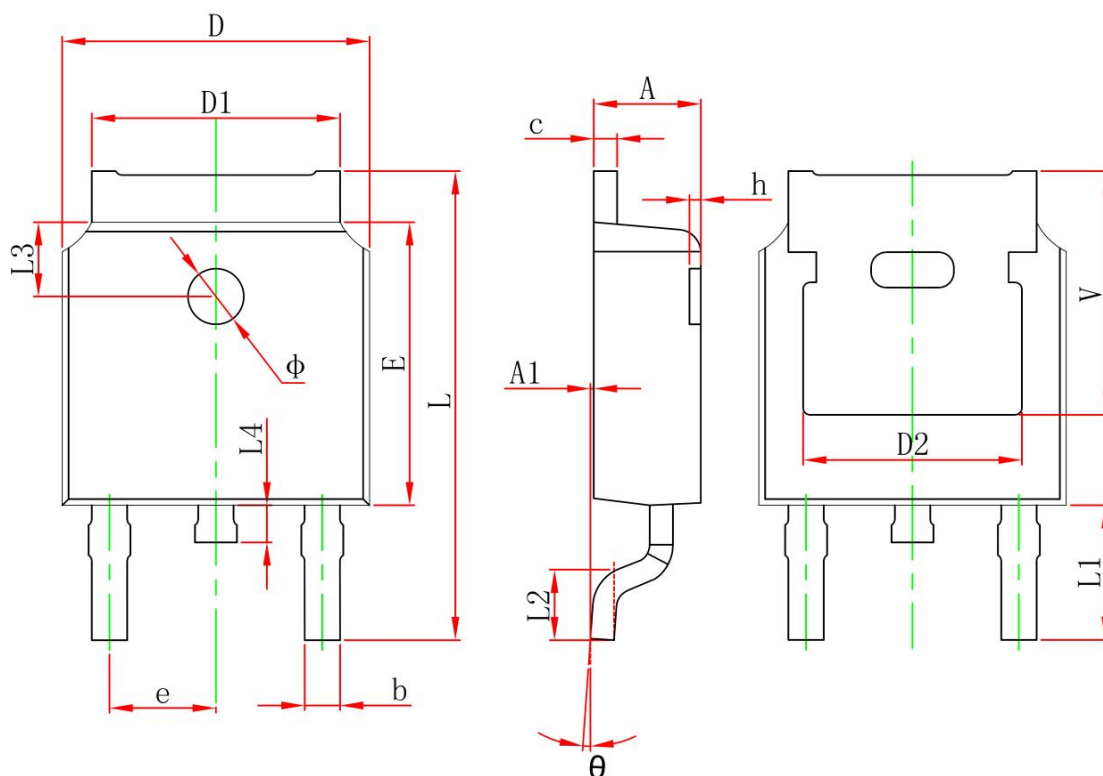
TO-252 Reel



Dimensions are in millimeter

Reel	D	D1	D2	W1	W2	I
13" Dia	330.00	100.00	Φ21.00	16.40	21.40	Φ13.00

Reel	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)
2500 pcs	13 inch	5000 pcs	360×360×65	25000 pcs	378×358×382

TO-252 Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
ϕ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 REF.		0.211 REF.	